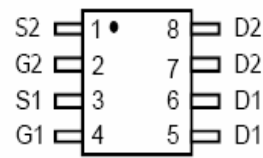
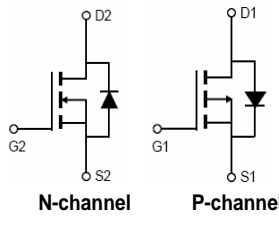
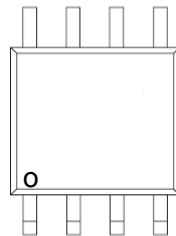


N and P-Channel Enhancement Mode Power MOSFET

<p>Description</p> <p>The 4616 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.</p> <p>General Features</p> <ul style="list-style-type: none"> ● N-Channel <ul style="list-style-type: none"> $V_{DS} = 30V, I_D = 8.0A$ $R_{DS(ON)} < 19m\Omega @ V_{GS}=10V$ $R_{DS(ON)} < 25m\Omega @ V_{GS}=4.5V$ ● P-Channel <ul style="list-style-type: none"> $V_{DS} = -30V, I_D = -7.0A$ $R_{DS(ON)} < 29m\Omega @ V_{GS}=-10V$ $R_{DS(ON)} < 38m\Omega @ V_{GS}=-4.5V$ ● High power and current handling capability ● Lead free product is acquired ● Surface mount package 	<p>SOP-8</p>  <p>Equivalent Circuit</p>  <p>MARKING</p>  <p>Y :year code W :week code</p>
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Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	30	-30	V
Gate-Source Voltage		V_{GS}	± 20	± 20	V
Continuous Drain Current	$T_A=25^\circ C$	I_D	8.0	-7.0	A
Pulsed Drain Current ^(Note 1)		I_{DM}	30	-30	A
Maximum Power Dissipation	$T_A=25^\circ C$	P_D	2.0	2.0	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 To 150	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note2)	$R_{\theta JA}$	N-Ch	62.5	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient ^(Note2)	$R_{\theta JA}$	P-Ch	62.5	$^\circ C/W$

SOP-8 Plastic-Encapsulate MOSFETS

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N-CH Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA

On Characteristics ^(Note 3)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.6	2.4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8A$	-	17	19	$m\Omega$
		$V_{GS}=4.5V, I_D=6A$	-	21	25	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=8A$	15	-	-	S

Dynamic Characteristics ^(Note 4)

Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	740	-	PF
Output Capacitance	C_{oss}		-	110	-	PF
Reverse Transfer Capacitance	C_{rss}		-	82	-	PF

Switching Characteristics ^(Note 4)

Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=2.5\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	5.0	-	nS
Turn-on Rise Time	t_r		-	3.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	19	-	nS
Turn-Off Fall Time	t_f		-	3.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=8A,$ $V_{GS}=10V$	-	15	-	nC
Gate-Source Charge	Q_{gs}		-	7.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3.5	-	nC

Drain-Source Diode Characteristics

Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=8A$	-	0.75	1.0	V
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Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

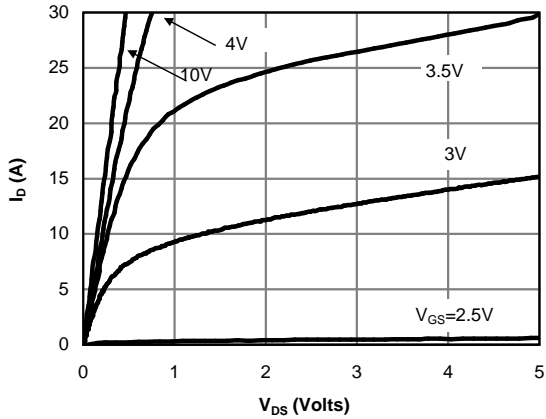


Fig 1: On-Region Characteristics (Note E)

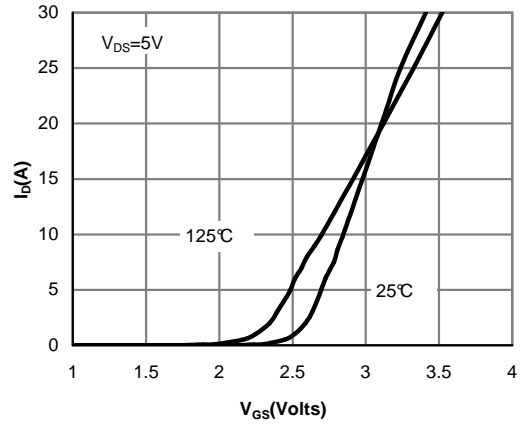


Figure 2: Transfer Characteristics (Note E)

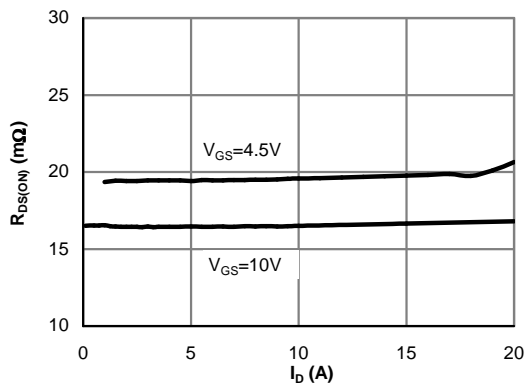


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

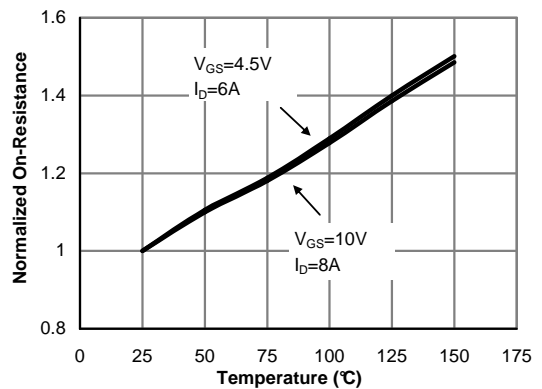


Figure 4: On-Resistance vs. Junction Temperature (Note E)

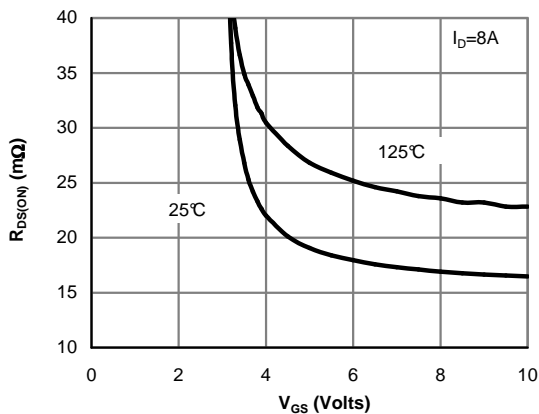


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

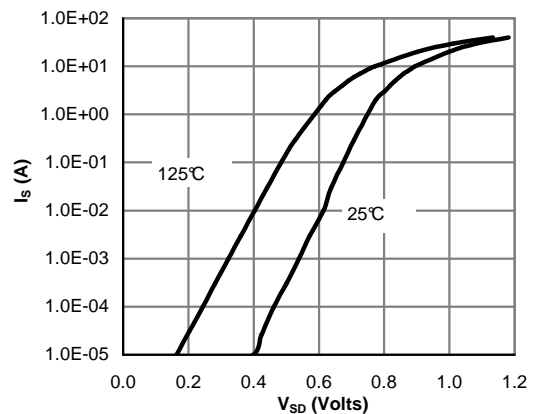


Figure 6: Body-Diode Characteristics (Note E)

N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

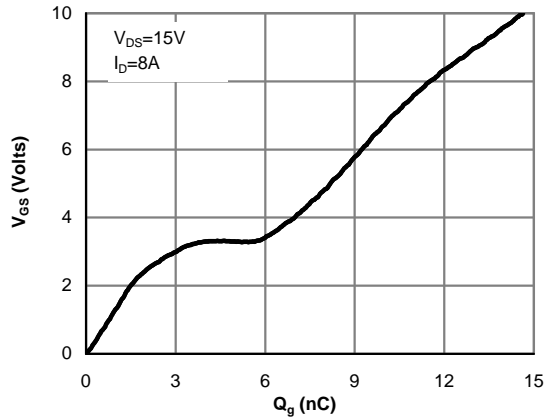


Figure 7: Gate-Charge Characteristics

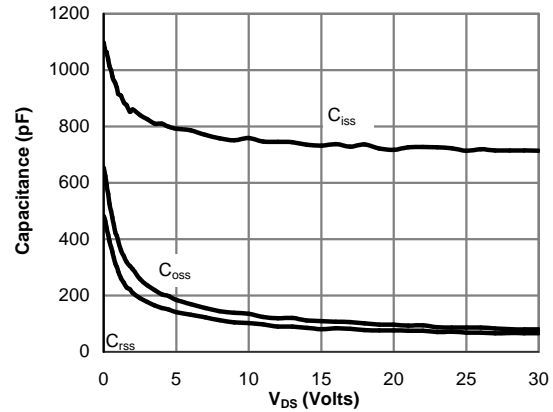


Figure 8: Capacitance Characteristics

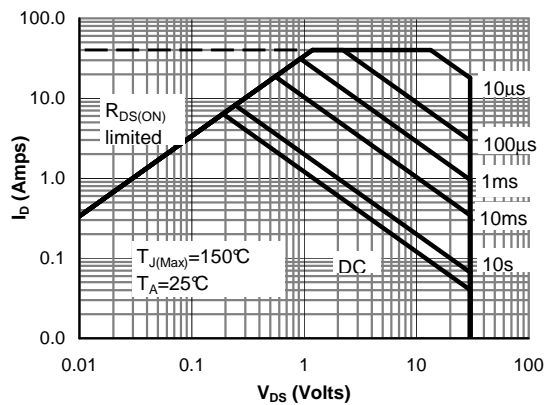


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

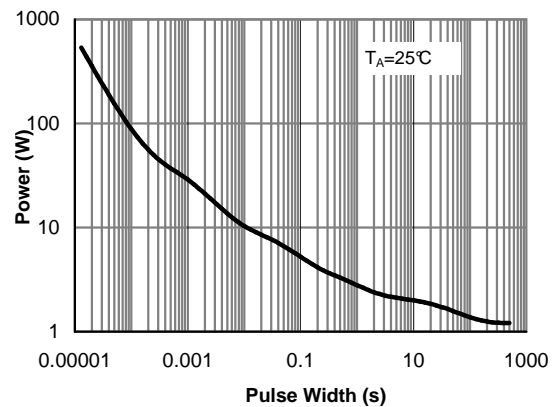


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

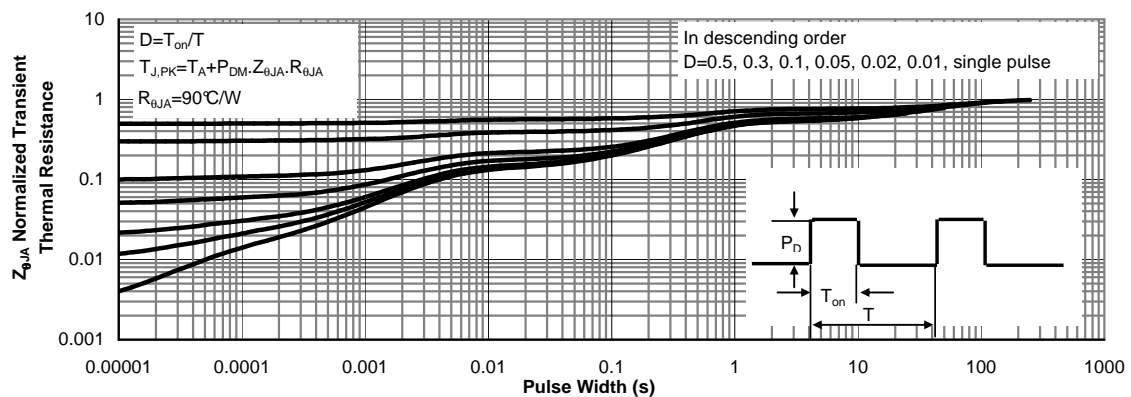
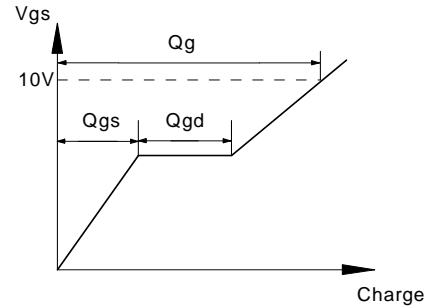
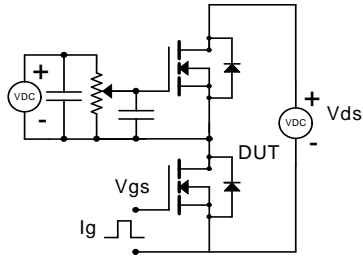


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

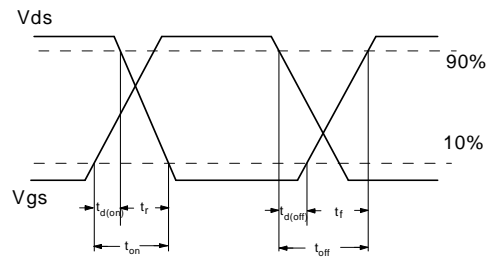
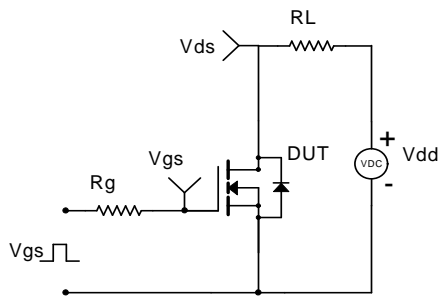
SOP-8 Plastic-Encapsulate MOSFETS

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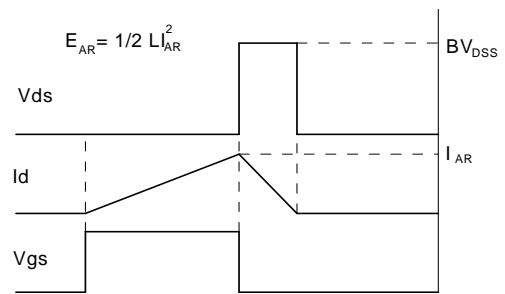
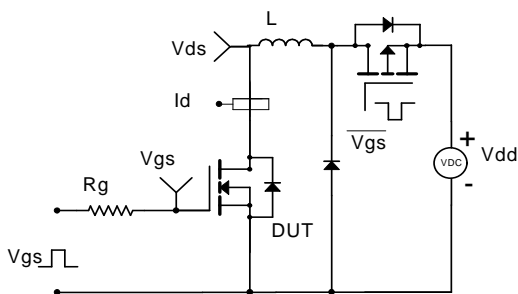
Gate Charge Test Circuit & Waveform



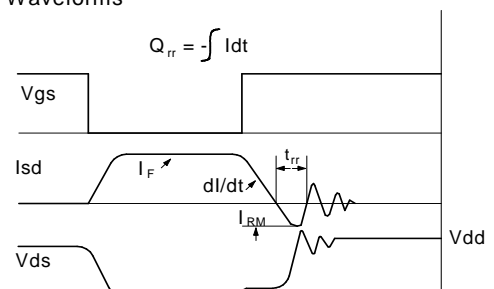
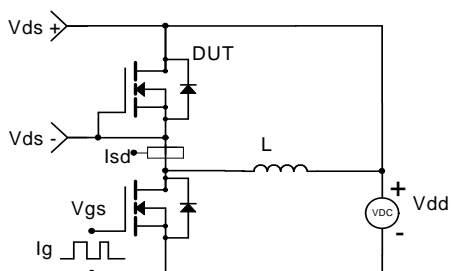
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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P-CH Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA

On Characteristics (Note 3)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.1	-1.4	-2.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-7.0A$ $V_{GS}=-4.5V, I_D=-5.0A$	-	26 34	29 38	m Ω m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-7.0A$	10	-	-	S

Dynamic Characteristics (Note 4)

Input Capacitance	C_{ISS}	$V_{DS}=-15V, V_{GS}=0V,$ $F=1.0MHz$	-	1040	-	PF
Output Capacitance	C_{OSS}		-	180	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	125	-	PF

Switching Characteristics (Note 4)

Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, R_L=2.3\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	10	-	nS
Turn-on Rise Time	t_r		-	5.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	nS
Turn-Off Fall Time	t_f		-	9	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-7.0A$ $V_{GS}=-10V$	-	19	-	nC
Gate-Source Charge	Q_{gs}		-	3.6	-	nC
Gate-Drain Charge	Q_{gd}		-	4.6	-	nC

Drain-Source Diode Characteristics

Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-7.0A$	-	0.75	-1.0	V
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Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

P-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

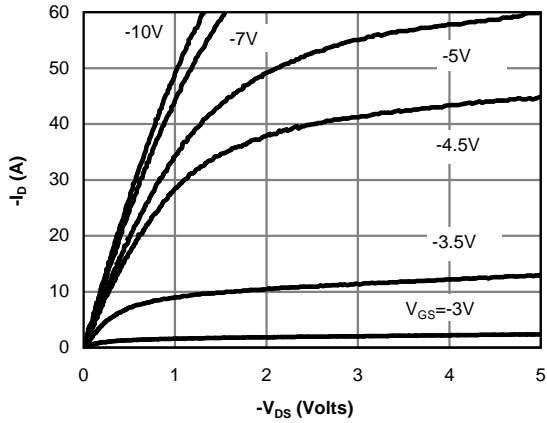


Fig 1: On-Region Characteristics (Note E)

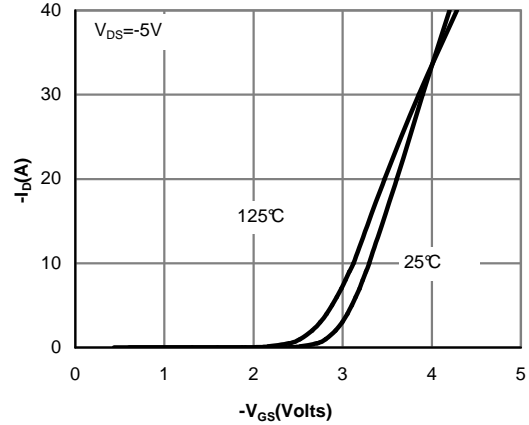


Figure 2: Transfer Characteristics (Note E)

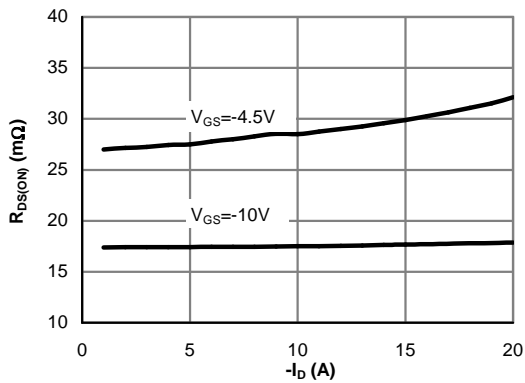


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

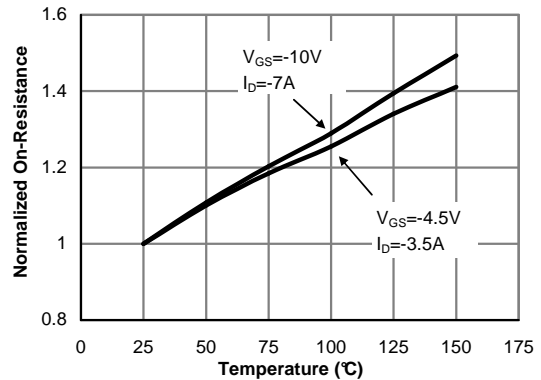


Figure 4: On-Resistance vs. Junction Temperature (Note E)

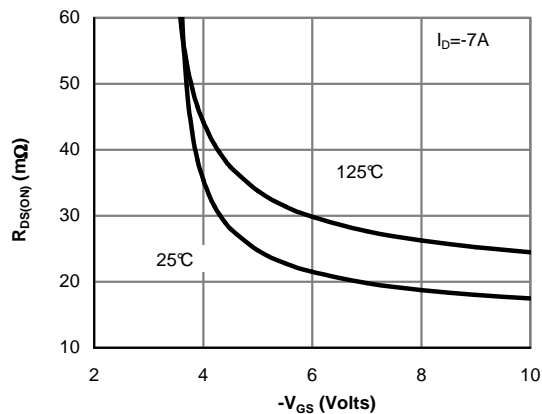


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

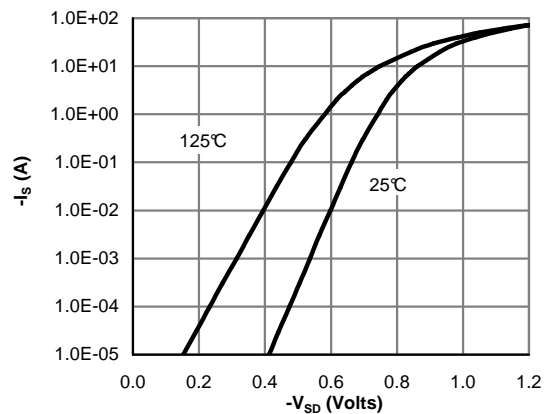


Figure 6: Body-Diode Characteristics (Note E)

P-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

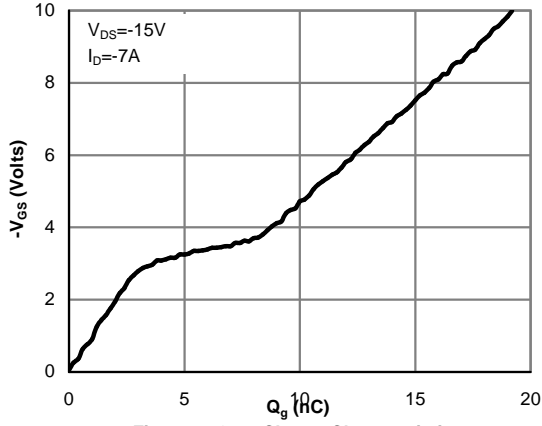


Figure 7: Gate-Charge Characteristics

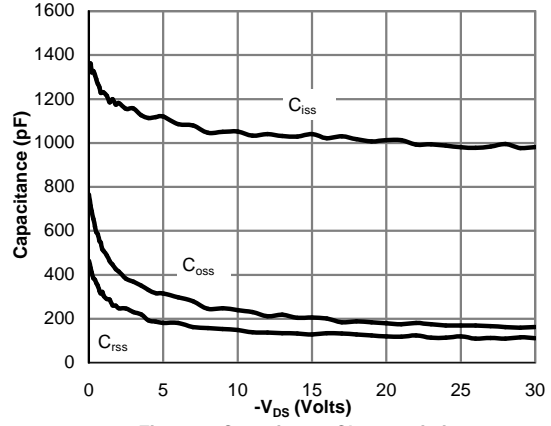


Figure 8: Capacitance Characteristics

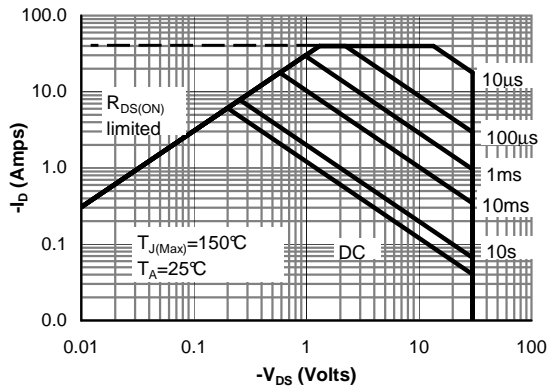


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

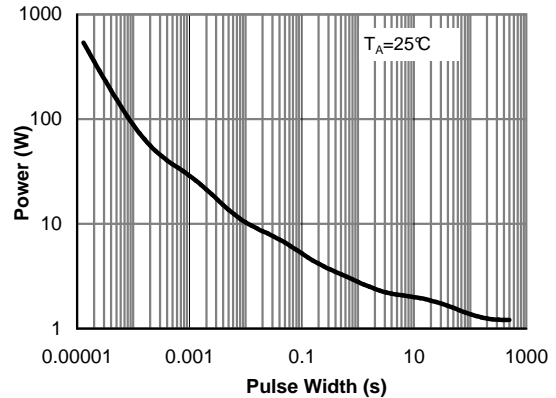


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

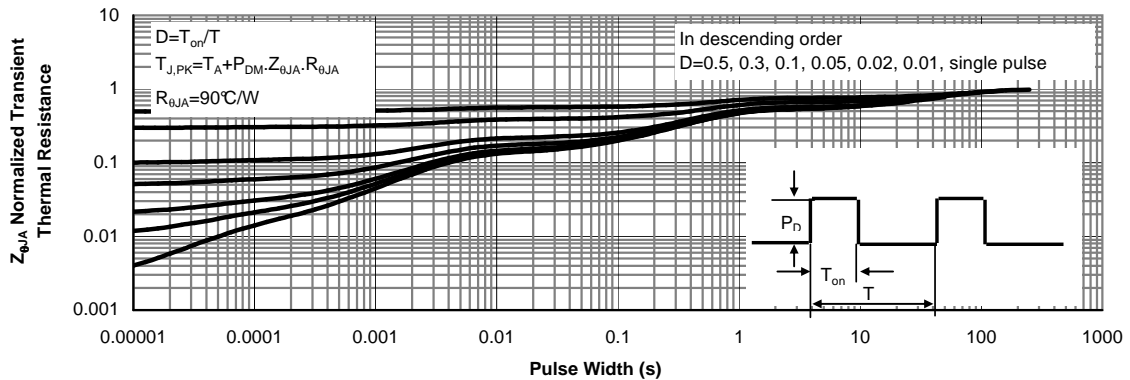
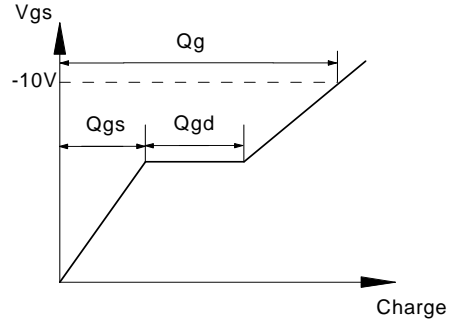
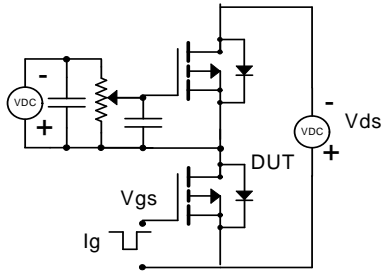


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

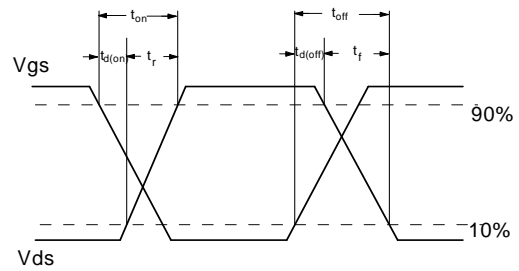
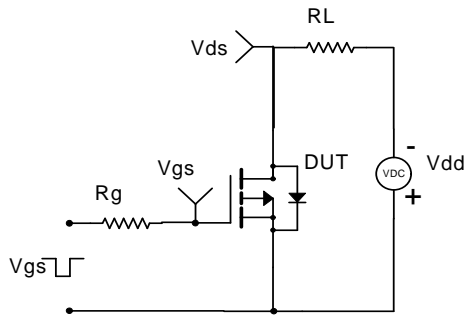
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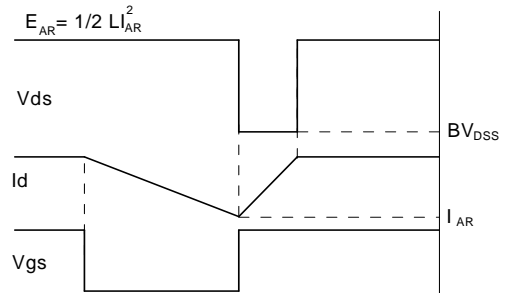
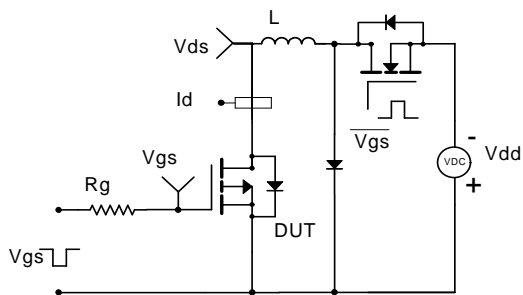
Gate Charge Test Circuit & Waveform



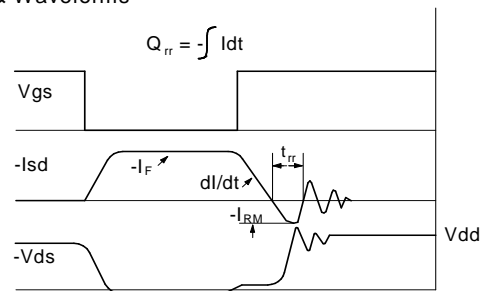
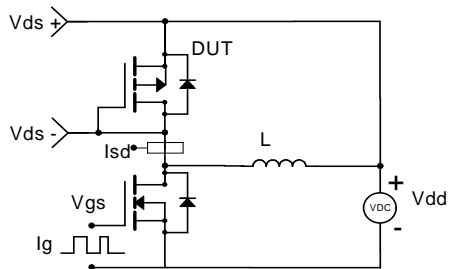
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



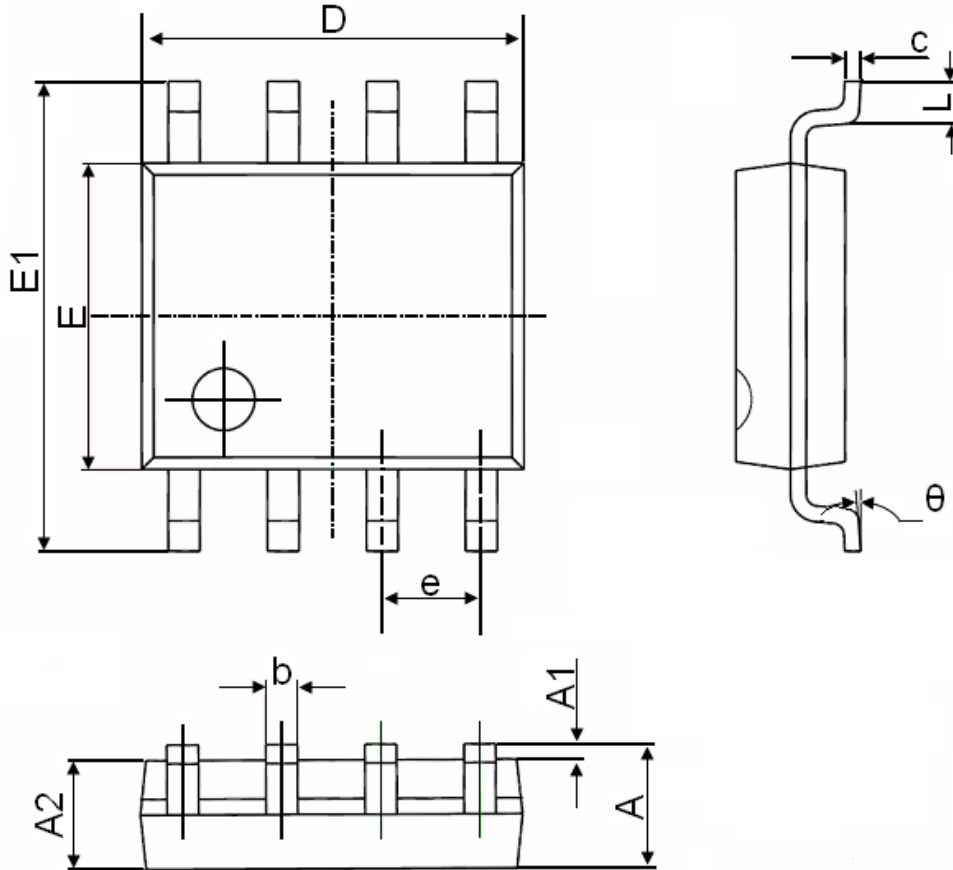
Diode Recovery Test Circuit & Waveforms



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SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°